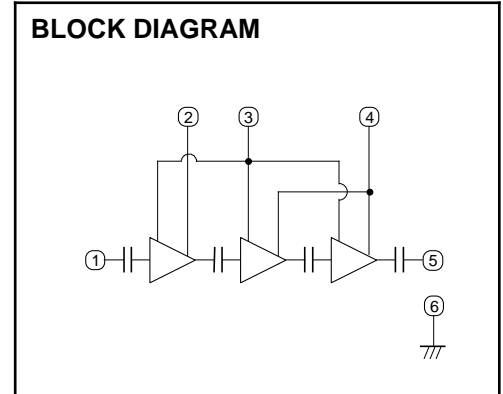
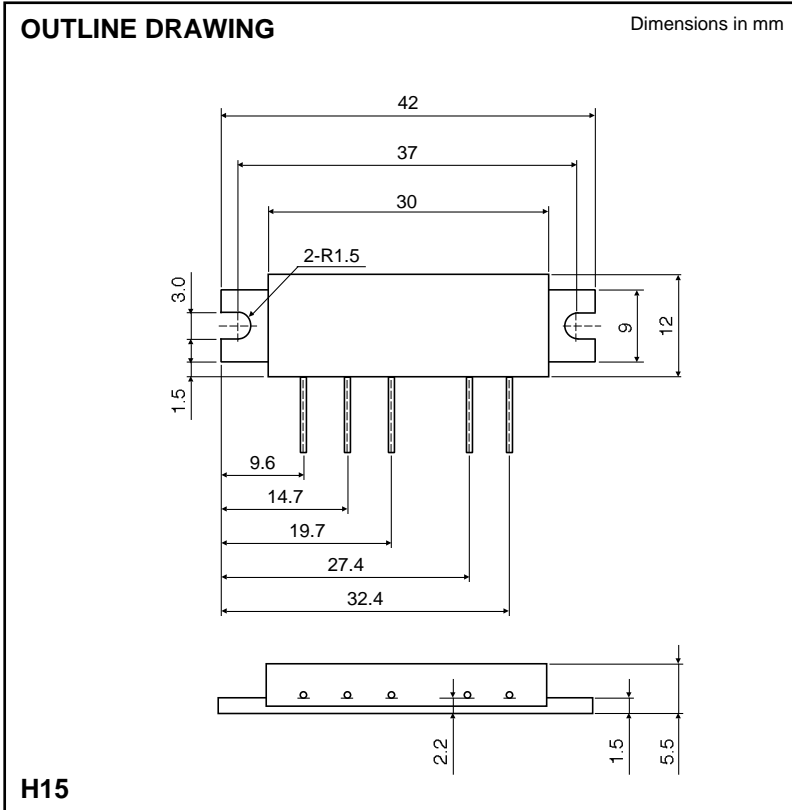


MITSUBISHI RF POWER MODULE  
**M68761**

SILICON MOS FET POWER AMPLIFIER, 820-851MHz, 6W, FM MOBILE RADIO



- PIN:
- ① Pin : RF INPUT
  - ② VDD1: 1st DRAIN BIAS SUPPLY
  - ③ VGG : GATE BIAS SUPPLY
  - ④ VDD2: 2nd DRAIN BIAS SUPPLY
  - ⑤ Po : RF OUTPUT
  - ⑥ GND: FIN

**ABSOLUTE MAXIMUM RATINGS** (Tc=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
VDD	Supply voltage	ZG=ZL=50	17	V
VGG	Gate bias voltage		4	V
Pin	Input power	f=820-851MHz, ZG=ZL=50	10	mW
Po	Output power	f=820-851MHz, ZG=ZL=50	10	W
Tc (OP)	Operation case temperature	f=820-851MHz, ZG=ZL=50	-30 to +100	°C
Tstg	Storage temperature		-40 to +100	°C

Note. Above parameters are guaranteed independently.

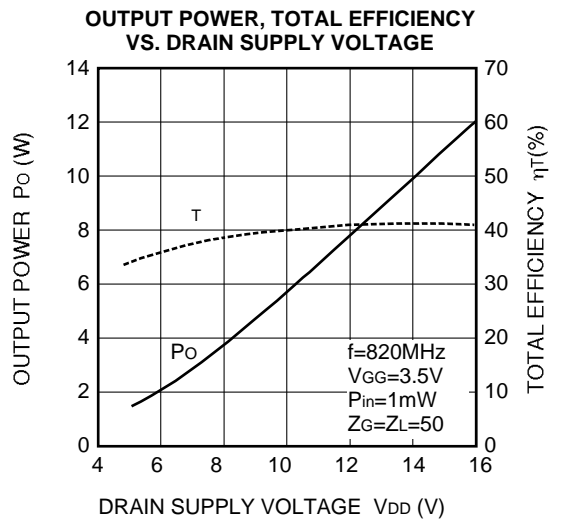
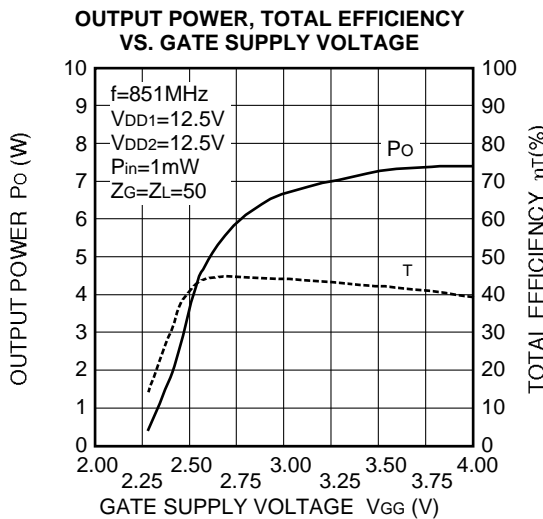
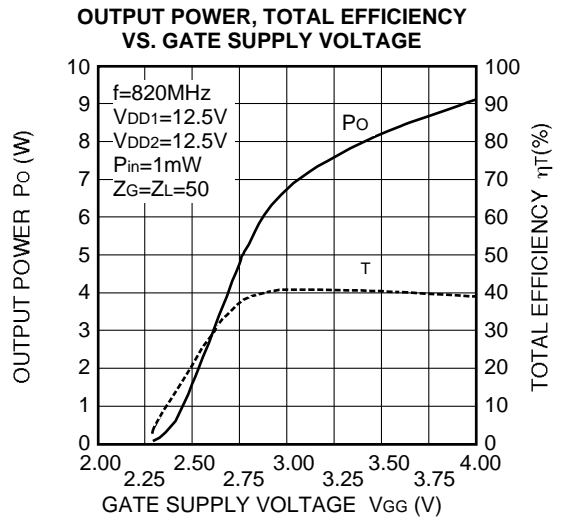
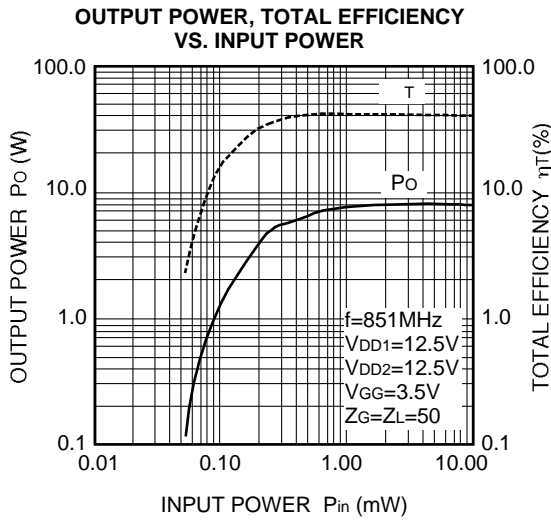
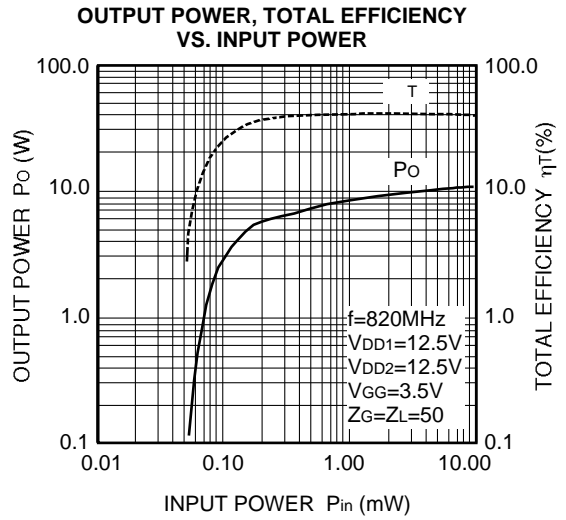
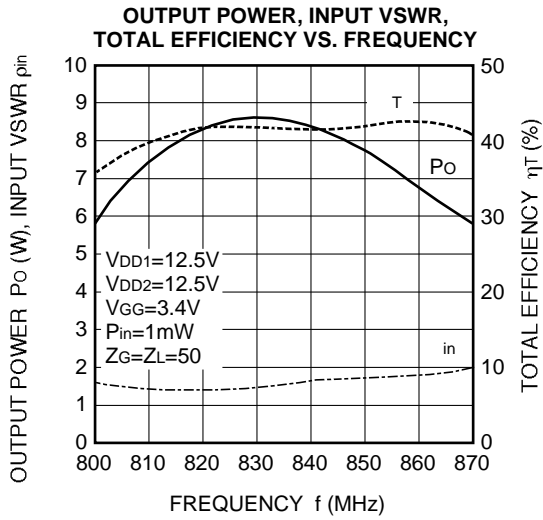
**ELECTRICAL CHARACTERISTICS** (Tc=25°C, ZG=ZL=50 unless otherwise noted)

Symbol	Parameter	Test conditions	Limits		Unit
			Min	Max	
f	Frequency range		820	851	MHz
Po	Output power	VDD=12.5V, VGG=3.5V, Pin=1mW, ZG=ZL=50	6		W
2fo	2nd. harmonic	Po=6W(VGG=Adjust), VDD=12.5V, Pin=1mW(CW), ZG=ZL=50		-30	dBc
in	Input VSWR			4	—
T	Total efficiency		33		%
—	Stability	ZG=ZL=50, VDD=10-16V, Load VSWR <4:1	No parasitic oscillation		—
—	Load VSWR tolerance	VDD=15.2V, Pin=1mW, Po=6W (VGG Adjust), ZL=20:1	No degradation or destroy		—

Note. Above parameters, ratings, limits and test conditions are subject to change.

**SILICON MOS FET POWER AMPLIFIER, 820-851MHz, 6W, FM MOBILE RADIO**

**TYPICAL PERFORMANCE DATA**



**SILICON MOS FET POWER AMPLIFIER, 820-851MHz, 6W, FM MOBILE RADIO**

